Ordering number:EN1719B

NPN Epitaxial Planar Silicon Transistor

2SD1620

1.5V, 3V Strobe Applications

Features

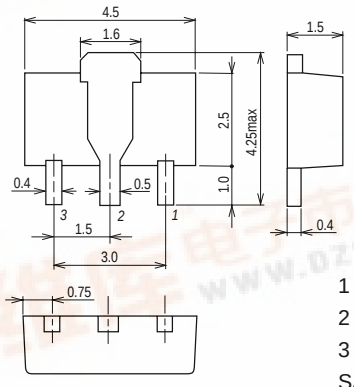
- Less power dissipation because of low $V_{CE(sat)}$, permitting more flashes of light to be emitted.
- Large current capacity and highly resistant to break-down.
- Excellent linearity of h_{FE} in the region from low current to high current.
- Ultrasmall size supports high-density, ultrasmall-sized hybrid IC designs.

Package Dimensions

unit:mm

2038A

[2SD1620]



1 : Base
2 : Collector
3 : Emitter
SANYO : PCP

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		30	V
Collector-to-Emitter Voltage	V_{CEX}		20	V
	V_{CEO}		10	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		3	A
Collector Current (Pulse)	I_{CP}		5	A
Collector Dissipation	P_C		500	mW
		Mounted on ceramic board (250mm^2×0.8mm)	1.3	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=20V, I_E=0			100	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			100	nA
DC Current Gain	h_{FE}	V_{CE}=2V, I_C=3A	140	210		
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=50mA		200		MHz
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		30		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3A, I_B=60mA		0.3	0.4	V

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SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEX}$	I_C=1mA, V_{BE}=3V	20			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	10			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	6			V